



TO-92 Plastic-Encapsulate Transistors

BC369

TRANSISTOR (PNP)

FEATURE

Power dissipation

 P_{CM} : 0.625 W ($T_{amb}=25^{\circ}C$)

Collector current

 I_{CM} : -1 A

Collector-base voltage

 $V_{(BR)CBO}$: -25 V

Operating and storage junction temperature range

 T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

TO-92

1. EMITTER
2. COLLECTOR
3. BASE



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-25		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10 mA, I_B = 0$	-20		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -25V, I_E = 0$		-10	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$		-10	μA
DC current gain	h_{FE}	$V_{CE} = -1V, I_C = -0.5mA$	85	375	
Collector-emitter voltage	$V_{CE(sat)}$	$I_C = -1A, I_B = -100mA$		-0.5	V
Base-emitter voltage	$V_{BE(on)}$	$I_C = -1A, V_{CE} = -1V$		-1	V
Transition frequency	f_T	$V_{CE} = -5V, I_C = -10mA$ $f = 20MHz$	65		MHz